

Amendments to the Claims

This listing of the Claims will replace all prior versions and listings of the claims in this patent application.

Listing of the Claims

Claims 1-14 (canceled)

15. (currently amended) A method for fabricating a circuit component, comprising:

providing a semiconductor wafer, a metal pad over said semiconductor wafer, a passivation layer over said semiconductor wafer, wherein an opening in said passivation layer is over said metal pad and exposes said metal pad, and a gold bump or pad layer over said semiconductor wafer, wherein said gold layer is connected to said metal pad through said opening; and

cleaning ion milling said gold layer, bump or pad, wherein said cleaning said gold bump or pad comprises ion milling; and

contacting said gold bump or pad with a testing probe.

Claim 16 (canceled)

17. (currently amended) The method of claim 15, wherein said ion milling said gold layer comprises using argon.

Claims 18-26 (canceled)

27. (currently amended) A method for fabricating a circuit component, comprising:

providing a semiconductor wafer, a metal pad over said semiconductor wafer, a passivation layer over said semiconductor wafer, wherein an opening in said passivation layer is over said metal pad and exposes said metal pad, and a noble-metal layer over said semiconductor wafer, wherein said noble-metal layer is connected to said metal pad through said opening; and forming a patterned metal bump over a semiconductor wafer, wherein said patterned metal bump has a top surface and a side wall discontinuously joined with said top surface;

ion milling said noble-metal layer. cleaning said patterned metal bump, wherein said cleaning said patterned metal bump comprises ion milling; and

contacting said patterned metal bump with a testing probe.

Claims 28 and 29 (canceled)

30. (currently amended) The method of claim 27, wherein said ion milling said noble-metal layer comprises using argon.

Claims 31-34 (canceled)

35. (new) The method of claim 15, after said ion milling said gold layer, further comprising contacting said gold layer with a testing probe.

36. (new) The method of claim 27, after said ion milling said noble-metal layer, further comprising contacting said noble-metal layer with a testing probe.